# In the Claims

- 1. (Previously Presented) A metallization stack in an integrated MEMS device, the
- 2 metallization stack comprising:
- a substrate having an electrically conductive structure;
- a field oxide, having a contact hole therein, formed over said substrate;
- 5 a silicide layer formed in said contact hole of said field oxide;
- a titanium-tungsten layer, formed directly on said silicide layer, to operatively contact
- 7 said electrically conductive structure in said substrate; and
- 8 a platinum layer;
- said platinum layer having a first portion formed directly on said titanium-tungsten layer;
- said platinum layer having a second portion formed directly on said field oxide;
- said silicide layer, said titanium-tungsten layer, and said platinum layer, together,
- forming an electrical connection to said electrically conductive structure.
- 2. (Previously Presented) The metallization stack of claim 1, wherein said electrically
- 2 conductive structure is an active silicon element.
- 3. (Previously Presented) The metallization stack of claim 2, wherein said contact hole
- 2 exposes a portion of a surface of said substrate at a bottom of said contact hole and said silicide
- 3 layer is formed only on the exposed portion of the surface of said substrate.

#### Claim 4 (Cancelled)

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5. (Previously Presented) The metallization stack of claim 1, wherein the integrated

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- 2 MEMS device is an optical MEMS.
- 6. (Previously Presented) The metallization stack of claim 1, wherein the integrated
- 2 MEMS device is a Bio-MEMS device.
- 7. (Previously Presented) The metallization stack of claim 6, wherein said platinum layer
- 2 forms a corrosive resistant electrode.
- 8. (Previously Presented) The metallization stack of claim 7, wherein said electrically
- 2 conductive structure is an interconnect of the Bio-MEMS device.

#### Claims 9-29 (Cancelled)

- 30. (Previously Presented) The metallization stack of claim 1, wherein said silicide layer
- 2 is a platinum silicide layer.

### Claim 31 (Cancelled)

- 32. (Previously Presented) A metallization stack in an integrated MEMS device, the
- 2 metallization stack comprising:
- a substrate having an electrically conductive structure;
- a field oxide formed over said substrate;
- a silicide layer formed on said field oxide;
- a titanium-tungsten layer, formed directly on said silicide layer, to operatively contact
- 7 said electrically conductive structure in said substrate; and
- 8 a platinum layer;

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- said platinum layer having a first portion formed directly on said titanium-tungsten layer;
  said platinum layer having a second portion formed directly on said field oxide.
- 33. (Previously Presented) The metallization stack of claim 32, wherein said electrically conductive structure is an active silicon element.

### Claim 34 (Cancelled)

- 35. (Previously Presented) The metallization stack of claim 32, wherein the integrated MEMS device is an optical MEMS.
- 36. (Previously Presented) The metallization stack of claim 32, wherein the integrated
  MEMS device is a Bio-MEMS device.
- 37. (Previously Presented) The metallization stack of claim 36, wherein said platinum layer forms a corrosive resistant electrode.
- 38. (Previously Presented) The metallization stack of claim 37, wherein said electrically conductive structure is an interconnect of the Bio-MEMS device.
- 39. (Previously Presented) The metallization stack of claim 32, wherein said silicide layer is a platinum silicide layer.

## Claims 40-62 (Cancelled)

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